

EABS21 THRU EABS26
SINGLE PHASE 2.0AMP SURFACE FAST GLASS PASSIVATED BRIDGE RECTIFIER

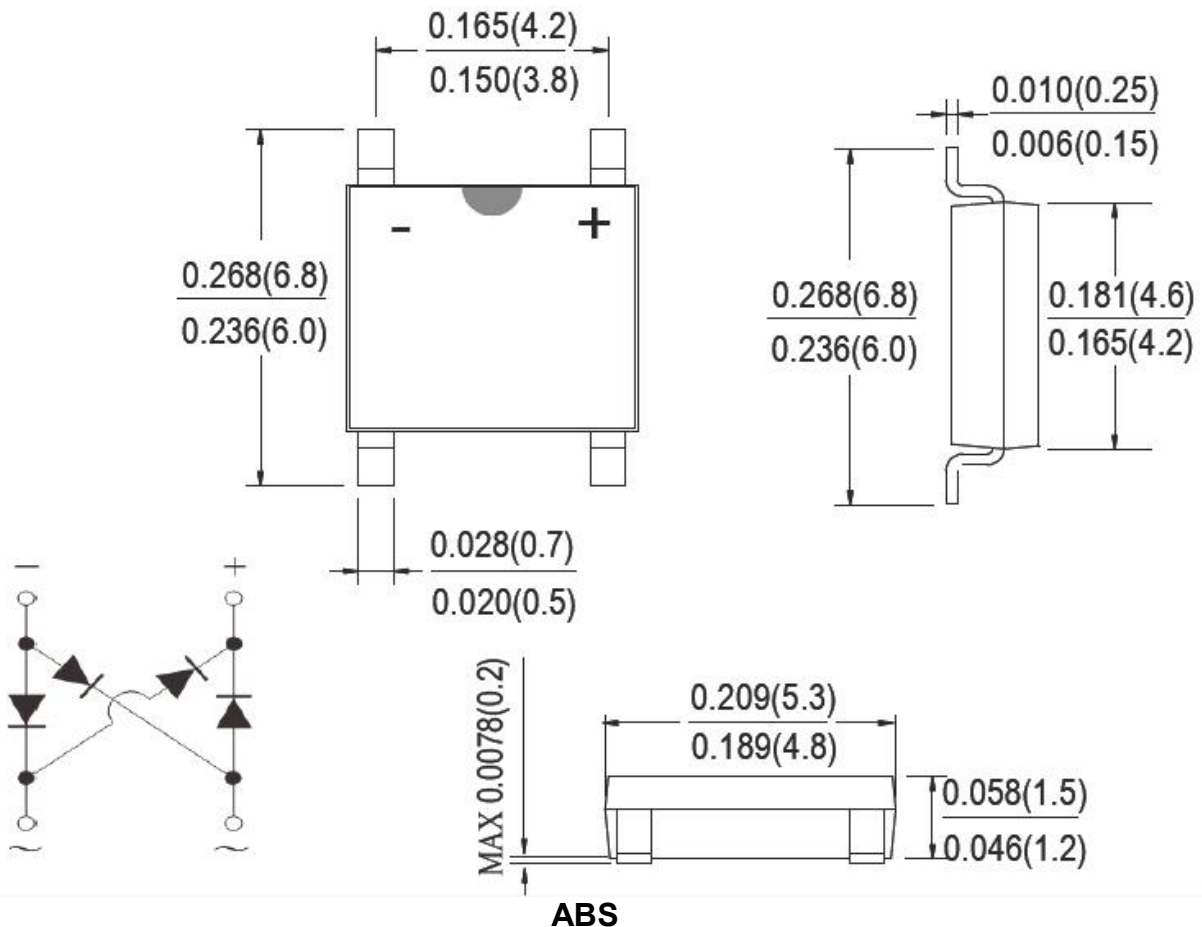
Features:

- Glass passivated die construction
- Low forward voltage drop
- High current capability
- High surge current capability
- Designed for surface mount application
- Plastic material-UL flammability 94V-0
- This is a Halogen Free Device
- All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request

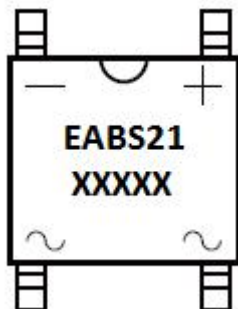
Mechanical Data:

- Case: SOPA-4, Molded plastic ABS
- Terminals: Plated leads solderable per MIL-STD-202, Method 208
- Polarity: as marked on case
- Mounting Position: Any

Mechanical Dimensions: In Inches/mm



Marking Diagram:



Where XXXXX is YYWWL

EABS21 = Part Name
YY = Year
WW = Week
L = Lot Number

Cautions: Molding resin
Epoxy resin UL:94V-0

Ordering Information:

Device	Package	Shipping
EABS21 THRU EABS26	ABS (Pb-Free)	5000pcs / reel

For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification.

Maximum Ratings and Electrical Characteristics @ $T_A=25^{\circ}\text{C}$ unless otherwise specified

Single Phase, half wave, 60Hz, resistive or inductive load.

For capacitive load, derate current by 20%.

Characteristic	Symbol	EABS21	EABS22	EABS24	EABS26	Units
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V_{RRM} V_{RWM} V_{DC}	100	200	400	600	V
RMS Reverse Voltage	V_{RMS}	70	140	280	420	V
Average Rectified Output Current @ $T_C=100^{\circ}\text{C}$	$I_{F(AV)}$	2.0				A
Non-Repetitive Peak Forward Surge Current 8.3ms Single half sine-wave superimposed on rated load(JEDEC Method)	I_{FSM}	60				A
Rating for fusing ($t<8.3\text{ms}$)	I^2t	14.94				A^2s
Forward Voltage per element @ $I_F=2.0\text{A}$	V_F	0.95		1.25	1.7	V
Maximum Reverse Recovery Time (Note 1)	T_{rr}	35				ns
Peak Reverse Current @ $T_A=25^{\circ}\text{C}$ At Rated DC Blocking Voltage @ $T_A=125^{\circ}\text{C}$	I_R	5.0 200				μA
Typical Thermal Resistance per leg	$R_{\theta JA}$	62.5				$^{\circ}\text{C/W}$
	$R_{\theta JL}$	25				
Junction Temperature	T_J	-55 to +150				$^{\circ}\text{C}$
Storage Temperature Range	T_{STG}	-55 to +150				$^{\circ}\text{C}$

Note:1. Reverse Recovery Test Conditions: $I_F=0.5\text{A}$, $I_R=1.0\text{A}$, $I_{RR}=0.25\text{A}$

FIG.1 FORWARD CURRENT DERATING CURVE

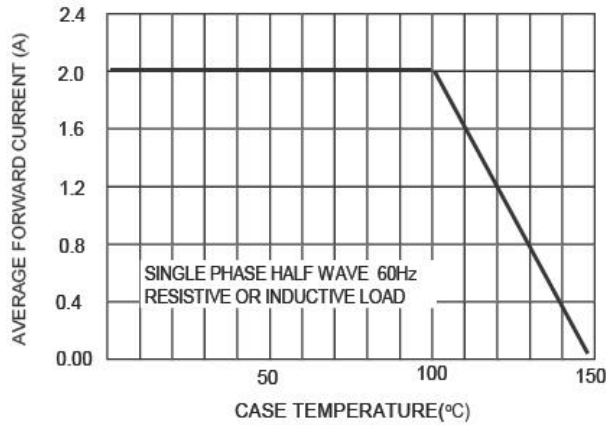


FIG.2 TYPICAL FORWARD CHARACTERISTICS

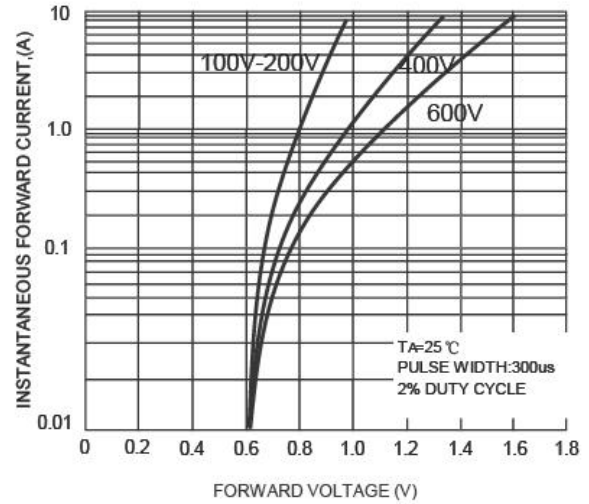


FIG.3 MAXIMUM NON-REPETITIVE

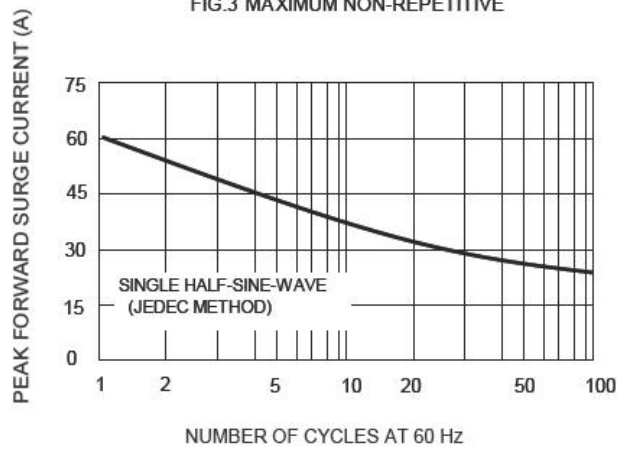
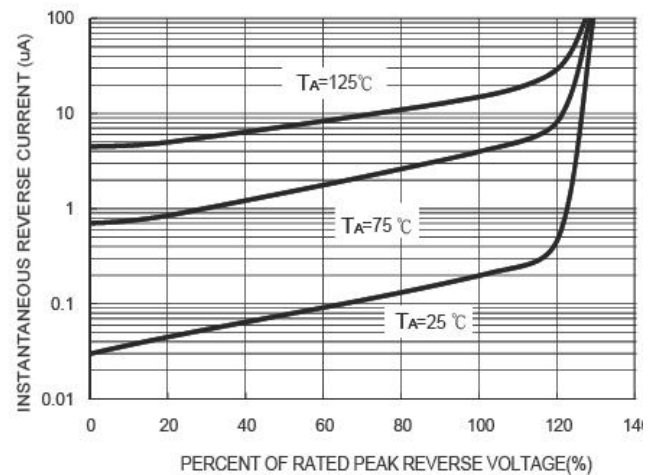
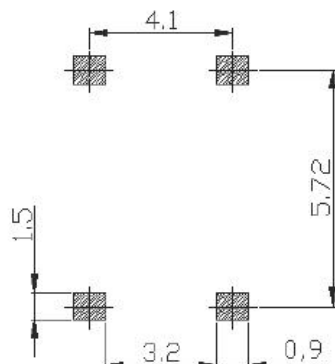


FIG. 4 TYPICAL REVERSE CHARACTERISTICS



ABS PAD LAYOUT





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